# Internally Compensated, High Performance Operational Amplifier

The MC1741C was designed for use as a summing amplifier, integrator, or amplifier with operating characteristics as a function of the external feedback components.

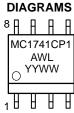
- No Frequency Compensation Required
- Short Circuit Protection
- Offset Voltage Null Capability
- Wide Common Mode and Differential Voltage Ranges
- Low Power Consumption
- No Latch Up



http://onsemi.com



PDIP-8 P1 SUFFIX CASE 626



**MARKING** 



SO-8 D SUFFIX CASE 751



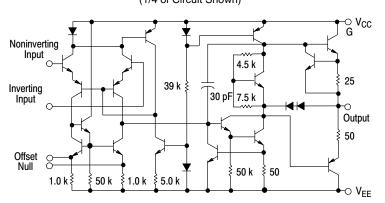
Datasheet.D

A = Assembly Location WL, L = Wafer Lot

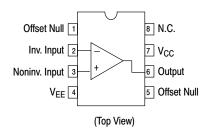
YY, Y = Year WW, W = Work Week

#### **Equivalent Circuit Schematic**

(1/4 of Circuit Shown)



#### **PIN CONNECTIONS**



#### ORDERING INFORMATION

Device	Package	Shipping
MC1741CD	SO-8	98 Units/Rail
MC1741CDR2	SO-8	2500 Tape & Reel
MC1741CP1	PDIP-8	50 Units/Rail

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Power Supply Voltage	V <sub>CC</sub> , V <sub>EE</sub>	±18	Vdc
Input Differential Voltage	V <sub>ID</sub>	±30	V
Input Common Mode Voltage (Note 1.)	V <sub>ICM</sub>	±15	V
Output Short Circuit Duration (Note 2.)	t <sub>SC</sub>	Continuous	_
Operating Ambient Temperature Range	T <sub>A</sub>	0 to +70	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +125	°C

For supply voltages less than +15 V, the absolute maximum input voltage is equal to the supply voltage.
 Supply voltage equal to or less than 15 V.

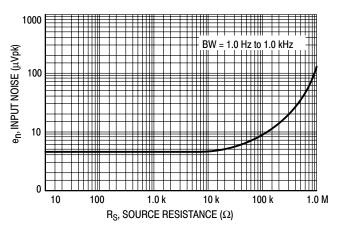
#### **ELECTRICAL CHARACTERISTICS** ( $V_{CC}$ = +15 V, $V_{EE}$ = -15 V, $T_A$ = 25°C, unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Input Offset Voltage (R <sub>S</sub> ≤ 10 k)	V <sub>IO</sub>	-	2.0	6.0	mV
Input Offset Current	I <sub>IO</sub>	-	20	200	nA
Input Bias Current	I <sub>IB</sub>	-	80	500	nA
Input Resistance	r <sub>i</sub>	0.3	2.0	-	ΜΩ
Input Capacitance	C <sub>i</sub>	_	1.4	-	pF
Offset Voltage Adjustment Range	V <sub>IOR</sub>	_	±15	-	mV
Common Mode Input Voltage Range	V <sub>ICR</sub>	±12	±13	-	V
Large Signal Voltage Gain ( $V_0 = \pm 10 \text{ V}, R_L \ge 2.0 \text{ k}$ )	A <sub>VOL</sub>	20	200	_	V/mV
Output Resistance	r <sub>o</sub>	-	75	_	Ω
Common Mode Rejection (R <sub>S</sub> ≤ 10 k)	CMR	70	90	_	dB
Supply Voltage Rejection (R <sub>S</sub> ≤ 10 k)	PSR	75	_	_	dB
Output Voltage Swing $ (R_L \ge 10 \text{ k}) $ $ (R_L \ge 2.0 \text{ k}) $	Vo	±12 ±10	±14 ±13	- -	V
Output Short Circuit Current	I <sub>SC</sub>	_	20	_	mA
Supply Current	I <sub>D</sub>	_	1.7	2.8	mA
Power Consumption	P <sub>C</sub>	-	50	85	mW
Transient Response (Unity Gain, Noninverting) $ (V_I = 20 \text{ mV},  R_L \geq \ 2.0 \text{ k},  C_L \leq 100 \text{ pF}) \text{ Rise Time} $ $ (V_I = 20 \text{ mV},  R_L \geq \ 2.0 \text{ k},  C_L \leq 100 \text{ pF}) \text{ Overshoot} $ $ (V_I = 10 \text{ V},  R_L \geq \ 2.0 \text{ k},  C_L \leq 100 \text{ pF}) \text{ Slew Rate} $	t <sub>TLH</sub> os SR	- - -	0.3 15 0.5	- - -	μs % V/μs

#### ELECTRICAL CHARACTERISTICS (V<sub>CC</sub> = +15 V, V<sub>FF</sub> = -15 V, T<sub>A</sub> = T<sub>low</sub> to T<sub>high</sub>, unless otherwise noted.)\*

Characteristic	Symbol	Min	Тур	Max	Unit
Input Offset Voltage ( $R_S \le 10 \text{ k}\Omega$ )	V <sub>IO</sub>	-	-	7.5	mV
Input Offset Current ( $T_A = 0^\circ$ to +70°C)	I <sub>IO</sub>	-	-	300	nA
Input Bias Current ( $T_A = 0^\circ$ to +70°C)	I <sub>IB</sub>	-	-	800	nA
Supply Voltage Rejection (R <sub>S</sub> ≤ 10 k)	PSR	75	-	-	dB
Output Voltage Swing (R <sub>L</sub> ≥ 2.0 k)	Vo	±10	±13	_	V
Large Signal Voltage Gain ( $R_L \ge 2.0 \text{ k}$ , $V_O = \pm 10 \text{ V}$ )	A <sub>VOL</sub>	15	-	-	V/mV

<sup>\*</sup>  $T_{low} = 0$ °C  $T_{high} = 70$ °C



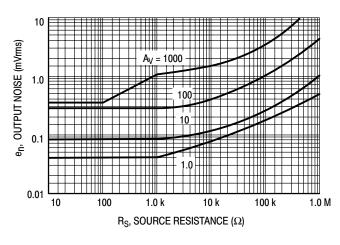
100 BW = 1.0 Hz to 1.0 kHz

1.0 10 100 1.0 10 k 100 k 1.0 M

R<sub>S</sub>, SOURCE RESISTANCE (Ω)

Figure 1. Burst Noise versus Source Resistance

Figure 2. RMS Noise versus Source Resistance



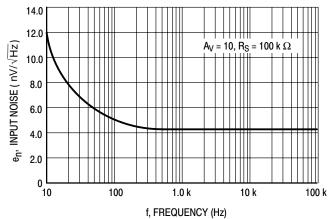
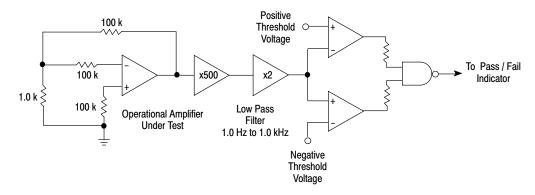


Figure 3. Output Noise versus Source Resistance

Figure 4. Spectral Noise Density



Unlike conventional peak reading or RMS meters, this system was especially designed to provide the quick response time essential to burst (popcorn) noise testing.

The test time employed is 10 sec and the 20 mV peak limit refers to the operational amplifier input thus eliminating errors in the closed loop gain factor of the operational amplifier.

Figure 5. Burst Noise Test Circuit

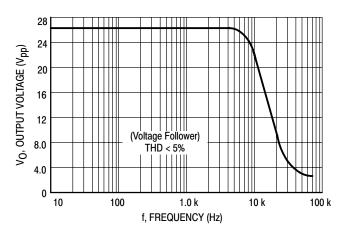


Figure 6. Power Bandwidth (Large Signal Swing versus Frequency)

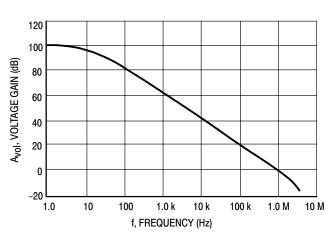


Figure 7. Open Loop Frequency Response

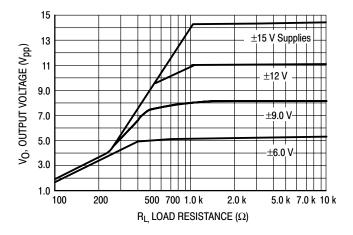


Figure 8. Positive Output Voltage Swing versus Load Resistance

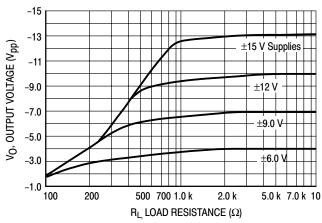


Figure 9. Negative Output Voltage Swing versus Load Resistance

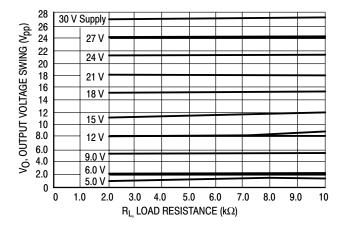


Figure 10. Output Voltage Swing versus Load Resistance (Single Supply Operation)

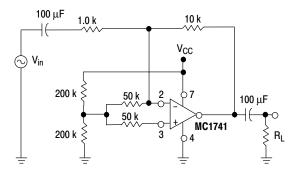


Figure 11. Single Supply Inverting Amplifier

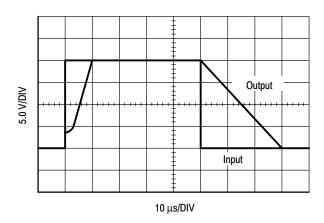


Figure 12. Noninverting Pulse Response

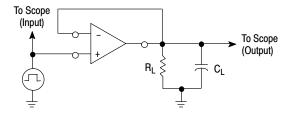


Figure 13. Transient Response Test Circuit

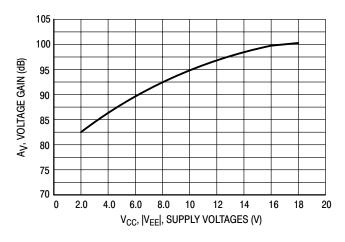
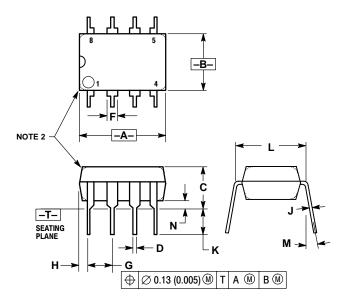


Figure 14. Open Loop Voltage Gain versus Supply Voltage

#### **PACKAGE DIMENSIONS**

#### PDIP-8 P1 SUFFIX CASE 626-05 ISSUE K



- NOTES:

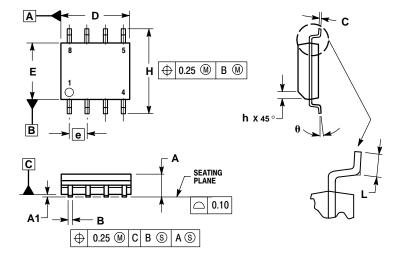
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- SQUARE CORNERS).

  3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.40	10.16	0.370	0.400
В	6.10	6.60	0.240	0.260
С	3.94	4.45	0.155	0.175
D	0.38	0.51	0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54 BSC		0.100 BSC	
Н	0.76	1.27	0.030	0.050
J	0.20	0.30	0.008	0.012
K	2.92	3.43	0.115	0.135
L	7.62 BSC		0.300	BSC
M		10°		10°
N	0.76	1.01	0.030	0.040

#### SO-8 **D SUFFIX** CASE 751-06 ISSUE T



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. DIMENSIONS ARE IN MILLIMETER.

  3. DIMENSION D AND E DO NOT INCLUDE MOLD PROTRUSION.

  4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

  5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SALL BE 0.127 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	1.35	1.75	
A1	0.10	0.25	
В	0.35	0.49	
С	0.19	0.25	
D	4.80	5.00	
E	3.80	4.00	
е	1.27 BSC		
Н	5.80	6.20	
h	0.25	0.50	
L	0.40	1.25	
A	0 °	7 °	

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